

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI HF15-28F is Designed for

FEATURES:

- $P_G = 21$ dB min. at 15 W/30 MHz
- $IMD_3 = -30$ dBc max. at 15 W_(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	40 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
q_{JC}	4.4 $^\circ C/W$

PACKAGE STYLE .380 4L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10602

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{CES}	$I_C = 200$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			2.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 200$ mA	5.0		---	---
C_{OB}	$V_{CB} = 30$ V $f = 1.0$ MHz			50	pF
G_P	$V_{CE} = 28$ V $f = 150$ MHz	10		---	dB
f_T	$V_{CE} = 10$ V $I_C = 200$ mA $f = 100$ MHz	250			MHz